EAST - [10795890.wsp:1]

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  - L1: (1806) semiconductor and hydrogen near anneal$3
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  - L4: (22) 2 and (anneal$3 with (polysilicon and gate$1))
  - L5: (603) semiconductor and hydrogen near anneal$31 and polysilicon
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5 and anneal$3 near polysilicon

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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	☐	☐	US 20040164297 A1	20040826	20	Display device	257/59	257/E21.413; 257/E21.703; 257/E27.111;
2	☐	☐	US 20040132270 A1	20040708	10	METHOD OF FORMING A NOVEL GATE ELECTRODE STRUCTURE COMPRISED OF A SILICON-GERMANIUM LAYER LOCATED BETWEEN	438/585	257/E21.198; 257/E29.155; 438/197;
3	☐	☐	US 20040056297 A1	20040325	24	Substrate device, method of manufacturing the same, electro-optical device, and electronic apparatus	257/306	438/30
4	☐	☐	US 20020070388 A1	20020613	9	LATERAL POLYSILICON PIN DIODE AND METHOD FOR SO FABRICATING	257/122	257/124; 257/141; 257/146;
5	☐	☐	US 20010052626 A1	20011220	9	Method for fabricating dual-gate structure	257/412	257/E21.632
6	☐	☐	US 6780741 B2	20040824	10	Method of forming a novel gate electrode structure comprised of a silicon-germanium layer located between random grained polysilicon layers	438/592	257/E21.198; 257/E29.155; 438/658;
7	☐	☐	US 6426547 B1	20020730	8	Lateral polysilicon pin diode and method for so fabricating	257/656	257/67; 257/75; 257/E29.336;
8	☐	☐	US 6084276 A	20000704	24	Threshold voltage tailoring of corner of MOSFET device	257/397	257/394; 257/404; 257/513;
9	☐	☐	US 5994202 A	19991130	24	Threshold voltage tailoring of the corner of a MOSFET device	438/433	257/354; 257/374; 257/386;
10	☐	☐	US 5424230 A	19950613	9	Method of manufacturing a polysilicon thin film transistor	438/166	148/DIG.1; 148/DIG.150; 148/DIG.90;
11	☐	☐	US 5111260 A	19920505	16	Polysilicon FETs	257/347	257/59; 257/E29.292; 430/319;

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